

All transistors have a length of 200nm

ECE 4203	Gate	NMOS	PMOS
		Wn (in nm)	Wp (in nm)
Banta Jr,Bryan James	NAND3	300	300
Barbour,Justin Richard	NAND3	400	400
Bui,David	NAND3	500	500
Burila,Ryan Jay Lacerna	NAND3	600	600
Chen,Keith Andrew	NAND3	700	700
Contreras,Francisco Ricardo	NAND3	800	800
Deleon,Josiah	NAND3	900	900
Erikson,John	NAND3	1000	1000
Garcia,Morley J	NAND3	1100	1100
Keenan,Colin Joseph	NAND3	1200	1200
Kidd,Timothy William	NAND4	300	300
Krischel,Cameron Jack	NAND4	400	400
Liang,Jinrun	NAND4	500	500
Lieu,Ian Edward	NAND4	600	600
Luc,Hao Phan Vinh	NAND4	700	700
Luktuke,Maithili Ashutosh	NAND4	800	800

Ly,Eric Giavi	NAND4	900	900
Malik,Yashika	NAND4	1000	1000
Manoukian,Edik	NAND4	1100	1100
Martinez Jr,Victor	NAND4	1200	1200
Mendoza,Victor Alfonso	NOR 3	300	300
Mora,Jessica	NOR 3	400	400
Moya,Orlando	NOR 3	500	500
Ngo,Jimmy	NOR 3	600	600
Nguyen,Aaron Kosaka	NOR 3	700	700
Nguyen,Cong Tran	NOR 3	800	800
Nguyen,Son Hai	NOR 3	900	900
Oh,Jay Hwan	NOR 3	1000	1000
Rufael,Yonas	NOR 3	1100	1100
Sadeli,Nigel Alvaro	NOR 3	1200	1200
Saucedo,Sally	NOR 4	300	300
Smith,Steeler Richard	NOR 4	400	400
Tippit,Mark Anthony	NOR-5	300	300

Vacheron,Tristan Ichiro	NOR-5	600	600
Tran,Anthony	NOR5	700	700
Vazquez,Jonathan Alberto	NOR5	800	800
Tran,Bang Tuong	NOR5	900	900
Wu, Cameron J	NOR5	1000	1000